

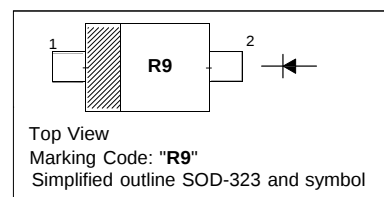
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- High speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Average Forward Current	I_O	300	mA
Maximum (Peak) Forward Current	I_{FM}	700	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 300\text{ mA}$	V_F	-	0.45	V
Reverse Current at $V_R = 20\text{ V}$	I_R	-	50	μA
Total Capacitance at $f = 1\text{ MHz}$	C_T	46	-	pF

